

Silicon Fast Recovery Diode

V_{RRM} = 100 V - 1000 V
I_F = 12 A

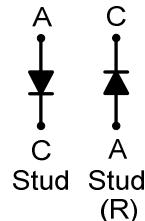
Features

- High Surge Capability
- Types up to 1000 V V_{RRM}

DO-4 Package

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	FR12B(R)05	FR12D(R)05	FR12G(R)05	FR12J(R)05	Unit
Repetitive peak reverse voltage	V _{RRM}		100	200	400	600	V
RMS reverse voltage	V _{RMS}		70	140	280	420	V
DC blocking voltage	V _{DC}		100	200	400	600	V
Continuous forward current	I _F	T _C ≤ 100 °C	12	12	12	12	A
Surge non-repetitive forward current, Half Sine Wave	I _{F,SM}	T _C = 25 °C, t _p = 8.3 ms	180	180	180	180	A
Operating temperature	T _j		-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C
Storage temperature	T _{stg}		-65 to 175	-65 to 175	-65 to 175	-65 to 175	°C

Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	FR12B(R)05	FR12D(R)05	FR12G(R)05	FR12J(R)05	Unit
Diode forward voltage	V _F	I _F = 12 A, T _j = 25 °C	1.4	1.4	1.4	1.4	V
Reverse current	I _R	V _R = 100 V, T _j = 25 °C	25	25	25	25	µA
Recovery Time							
Maximum reverse recovery time	T _{RR}	I _F =0.5 A, I _R =1.0 A, I _{RR} = 0.25 A	500	500	500	500	nS
Thermal characteristics							
Thermal resistance, junction - case	R _{thJC}		2.0	2.0	2.0	2.0	°C/W

